

MMGTU200D120B6C

1200V 200A IGBT Module

September 2016

Version 02

RoHS Compliant

APPLICATIONS

Unit

W

Unit
V

A²S

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$I_F(A)$

$V_F(V)$

Figure 9. Diode Forward Characteristics Diode -inverter

$E_{REC}(mJ)$

Rg

Figure 10. Switching Energy vs Gate Resistor Diode - inverter

$E_{REC}(mJ)$

$I_{F,AD}$

Figure 11. Switching Energy vs Forward Current Diode-inverter

$Z_{th,dc}(K/W)$

Rectangular Pulse Duration t_{SD}

Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

